

<b>SANYO</b>	No.572D	<b>2SA1016,1016K/2SC2362, 2362K</b>
		PNP/NPN Epitaxial Planar Silicon Transistors <b>High-Voltage Low-Noise Amp Applications</b>

( ): 2SA1016, 1016K

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$		2SA1016, 2SC2362	2SA1016K, 2SC2362K	unit
Collector to Base Voltage	$V_{CB0}$	(-) 120	(-) 150	V
Collector to Emitter Voltage	$V_{CE0}$	(-) 100	(-) 120	V
Emitter to Base Voltage	$V_{EBO}$		(-) 5	V
Collector Current	$I_C$		(-) 50	mA
Collector Current(Pulse)	$I_{CP}$		(-) 100	mA
Collector Dissipation	$P_C$		400	mW
Junction Temperature	$T_j$		125	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		-55 to +125	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=(-) 80\text{V}, I_E=0$			(-) 1.0	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=(-) 4\text{V}, I_C=0$			(-) 1.0	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE}=(-) 6\text{V}, I_C=(-) 1\text{mA}$	160*		960*	
Gain-Bandwidth Product	$f_T$	$V_{CE}=(-) 6\text{V}, I_C=(-) 1\text{mA}$		(110) 130		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=(-) 10\text{V}, f=1\text{MHz}$		(2.2) 1.8		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-) 10\text{mA}, I_B=(-) 1\text{mA}$			(-) 0.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-) 10\mu\text{A}, I_E=0$	(-) 120			V
		[A1016, C2362]				
		$I_C=(-) 10\mu\text{A}, I_E=0$	(-) 150			V
		[A1016K, C2362K]				
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-) 1\text{mA}, R_{BE}=\infty$	(-) 100			V
		[A1016, C2362]				
		$I_C=(-) 1\text{mA}, R_{BE}=\infty$	(-) 120			V
		[A1016K, C2362K]				
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-) 10\mu\text{A}, I_C=0$	(-) 5			V
Noise Level	$V_{NO(ave)}$	$V_{CC}=30\text{V}, I_C=1\text{mA}, R_g=56\text{k}\Omega$ $V_G=77\text{dB}/1\text{kHz}$			35	mV
Noise Peak Level	$V_{NO(peak)}$	" " "			200	mV

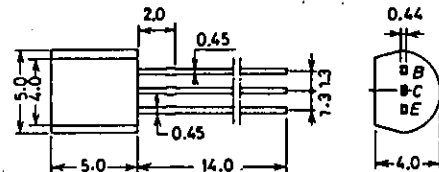
\* The 2SA1016,K / 2SC2362,K are classified by 1mA  $h_{FE}$  as follows :

160	F	320	280	G	560	480	H	960
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**Package Dimensions**

(unit: mm)

2003A



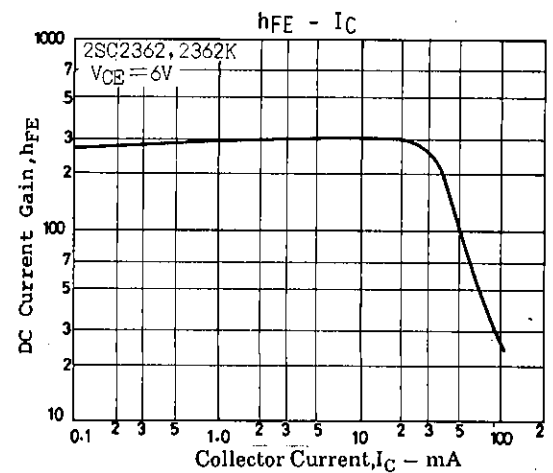
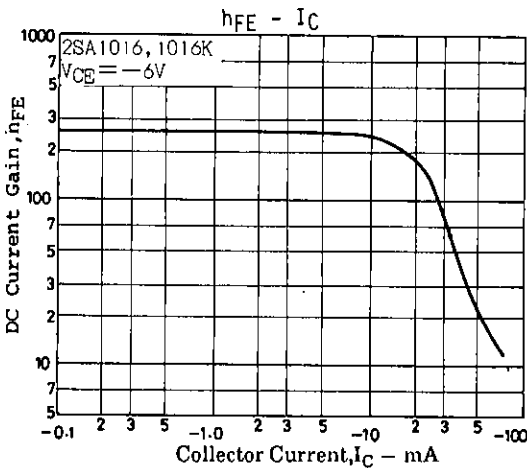
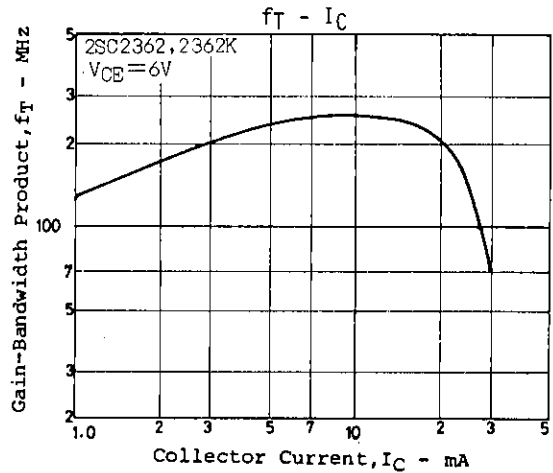
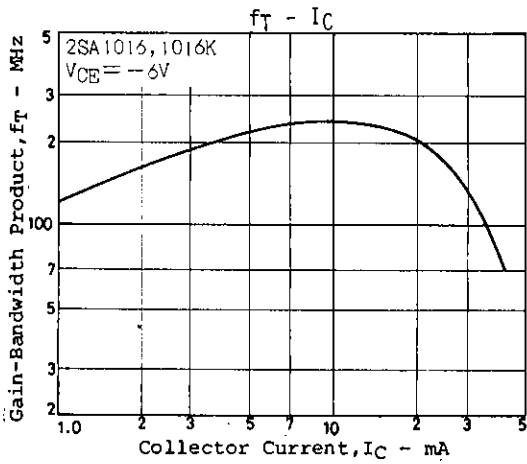
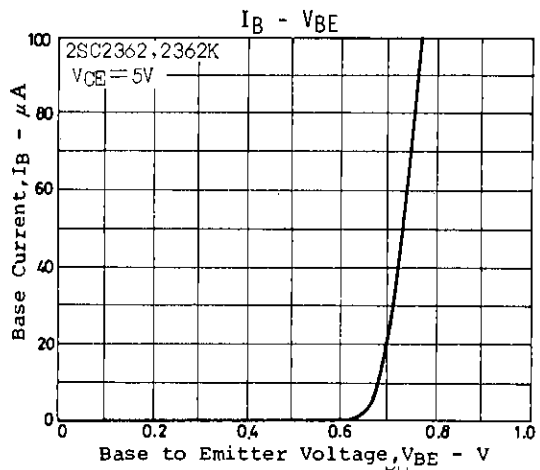
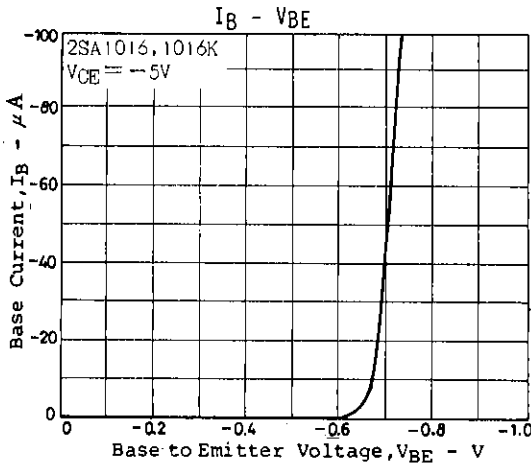
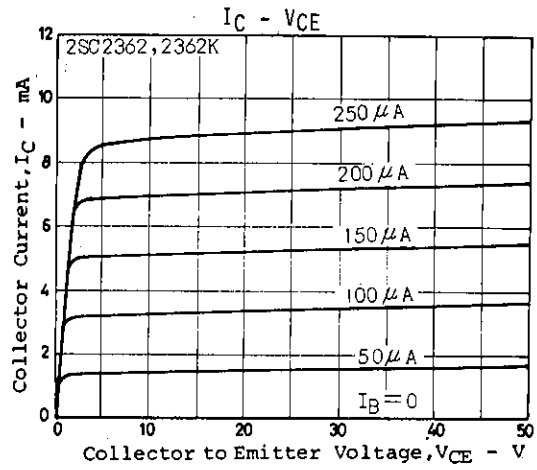
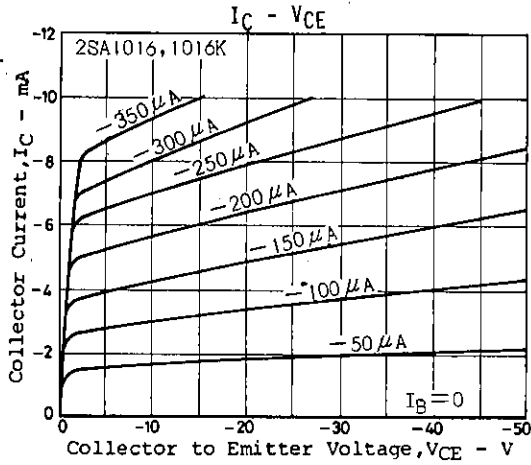
JEDEC: TO-92  
EIAJ : SC-43  
SANYO: NP

B. Base  
C. Collector  
E. Emitter

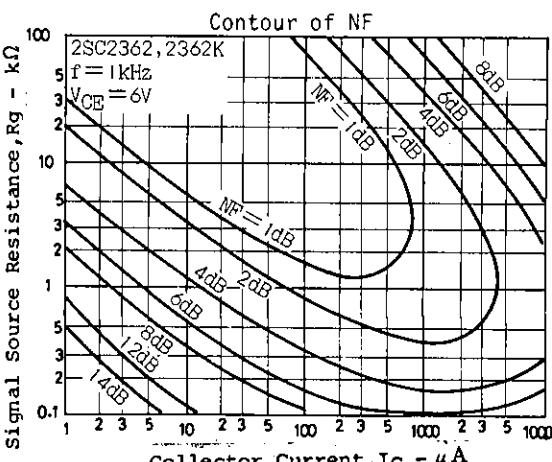
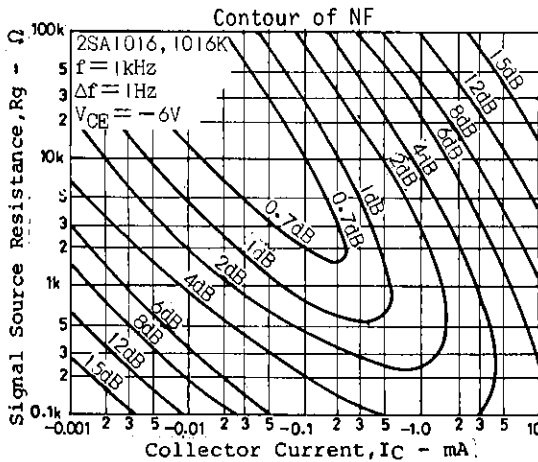
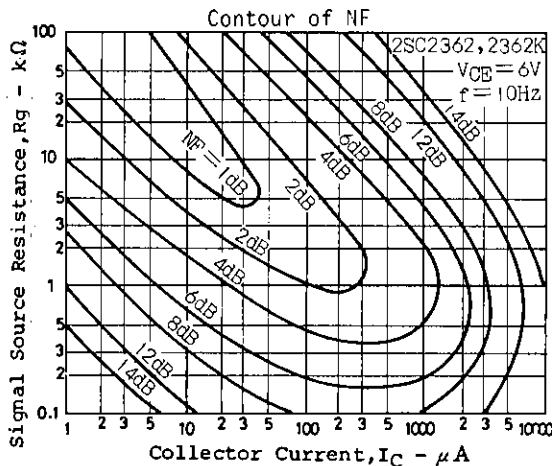
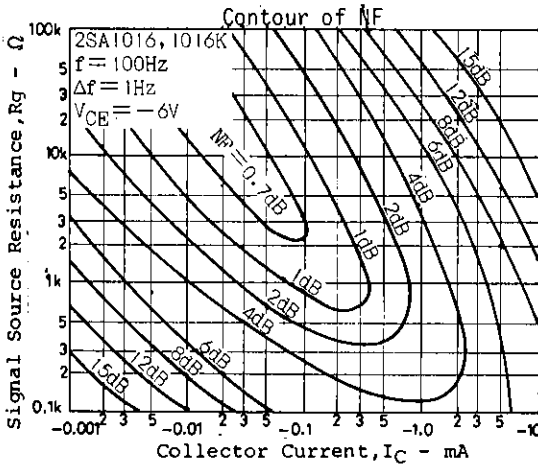
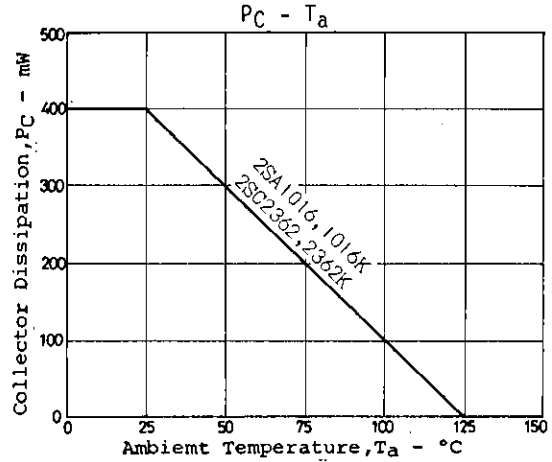
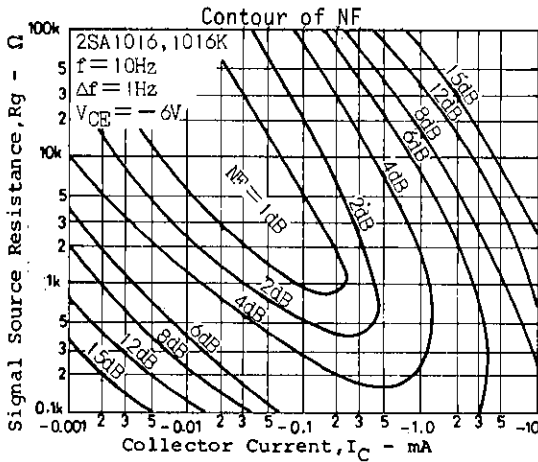
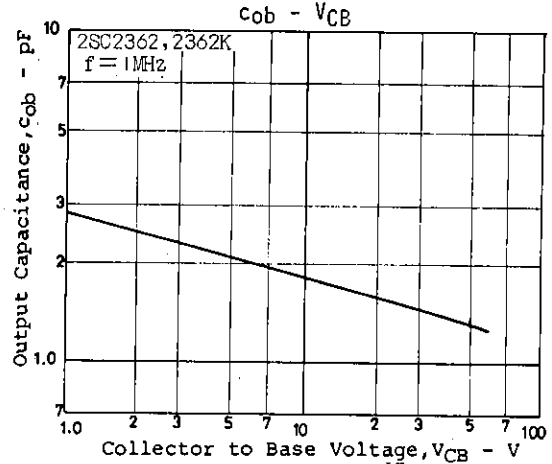
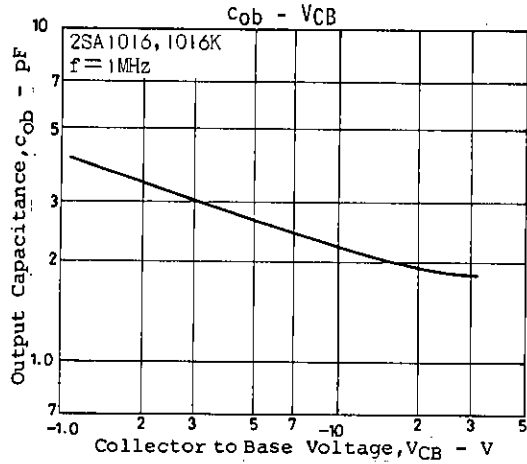
**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**

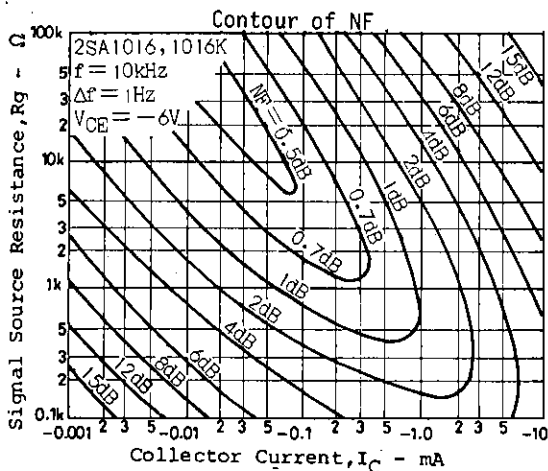
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